

ABSTRACT OF THE DISCLOSURE

A MOSFET structure comprises a tortuous gate having a first sidewall and a second sidewall, disposed over a semiconductor substrate. A source region is disposed within the semiconductor substrate adjacent to the first sidewall of the tortuous gate.

- 5 The source region comprises a broader part and a narrower part. Contacts are positioned above the broader part of the source region and are in contact with the broader part of the source region. A drain region is disposed within the semiconductor substrate adjacent to the second sidewall of the tortuous gate. The drain region comprises a broader part and a narrower part. Contacts are disposed above the broader part of the
- 10 drain region and are in contact with the broader part of the drain region. The broader part of the drain region is disposed opposite to the narrower part of the source region. The narrower part of the drain region is disposed opposite to the broader part of the source region.

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